

INTERNATIONAL STANDARD



**Semiconductor devices – Micro-electromechanical devices –
Part 36: Environmental and dielectric withstand test methods for MEMS
piezoelectric thin films**



THIS PUBLICATION IS COPYRIGHT PROTECTED

Copyright © 2019 IEC, Geneva, Switzerland

All rights reserved. Unless otherwise specified, no part of this publication may be reproduced or utilized in any form or by any means, electronic or mechanical, including photocopying and microfilm, without permission in writing from either IEC or IEC's member National Committee in the country of the requester. If you have any questions about IEC copyright or have an enquiry about obtaining additional rights to this publication, please contact the address below or your local IEC member National Committee for further information.

IEC Central Office
3, rue de Varembe
CH-1211 Geneva 20
Switzerland

Tel.: +41 22 919 02 11
info@iec.ch
www.iec.ch

About the IEC

The International Electrotechnical Commission (IEC) is the leading global organization that prepares and publishes International Standards for all electrical, electronic and related technologies.

About IEC publications

The technical content of IEC publications is kept under constant review by the IEC. Please make sure that you have the latest edition, a corrigendum or an amendment might have been published.

IEC publications search - webstore.iec.ch/advsearchform

The advanced search enables to find IEC publications by a variety of criteria (reference number, text, technical committee,...). It also gives information on projects, replaced and withdrawn publications.

IEC Just Published - webstore.iec.ch/justpublished

Stay up to date on all new IEC publications. Just Published details all new publications released. Available online and once a month by email.

IEC Customer Service Centre - webstore.iec.ch/csc

If you wish to give us your feedback on this publication or need further assistance, please contact the Customer Service Centre: sales@iec.ch.

Electropedia - www.electropedia.org

The world's leading online dictionary on electrotechnology, containing more than 22 000 terminological entries in English and French, with equivalent terms in 16 additional languages. Also known as the International Electrotechnical Vocabulary (IEV) online.

IEC Glossary - std.iec.ch/glossary

67 000 electrotechnical terminology entries in English and French extracted from the Terms and Definitions clause of IEC publications issued since 2002. Some entries have been collected from earlier publications of IEC TC 37, 77, 86 and CISPR.

INTERNATIONAL STANDARD



**Semiconductor devices – Micro-electromechanical devices –
Part 36: Environmental and dielectric withstand test methods for MEMS
piezoelectric thin films**

INTERNATIONAL
ELECTROTECHNICAL
COMMISSION

ICS 31.080.99; 31.140

ISBN 978-2-8322-6720-2

Warning! Make sure that you obtained this publication from an authorized distributor.

CONTENTS

FOREWORD.....	3
INTRODUCTION.....	5
1 Scope.....	6
2 Normative references	6
3 Terms and definitions	6
4 Testing procedure.....	6
4.1 General.....	6
4.2 Initial measurements.....	7
4.3 Tests	7
4.3.1 DUT setup and environmental conditions	7
4.3.2 Test duration	7
4.3.3 Number of tests and number of DUTs	7
4.4 Post treatment	8
4.5 Final measurements.....	8
5 Environmental and dielectric withstand testing.....	8
5.1 Environmental testing.....	8
5.1.1 General	8
5.1.2 High temperature bias test.....	9
5.1.3 High temperature and high humidity bias test	9
5.1.4 High temperature storage	9
5.1.5 Low temperature storage.....	10
5.1.6 High temperature and high humidity storage	10
5.1.7 Soldering heat test	10
5.1.8 Temperature cycling test	11
5.2 Dielectric withstand testing	12
Annex A (informative) Report of test results	14
A.1 General.....	14
A.2 Environmental test	14
A.3 Dielectric withstand test	14
Bibliography.....	16
Figure 1 – Flow of the testing procedure	7
Figure 2 – Temperature profile for reflow soldering with lead-free solder.....	11
Figure 3 – Temperature profile of the temperature cycling test.....	12
Figure 4 – Example of a dielectric withstand test circuit for DC voltage	13
Figure A.1 – I-V measurement	15
Figure A.2 – Optical image of top electrodes before and after breakdown	15
Table 1 – Selectable test conditions.....	9
Table 2 – Selectable test conditions.....	10
Table 3 – Soldering heat test condition	10
Table 4 – Conditions of temperature profile for reflow soldering with lead-free solder	11
Table A.1 – High-temperature test	14
Table A.2 – Dielectric withstand test	15

INTERNATIONAL ELECTROTECHNICAL COMMISSION

SEMICONDUCTOR DEVICES – MICRO-ELECTROMECHANICAL DEVICES –

Part 36: Environmental and dielectric withstand test methods for MEMS piezoelectric thin films

FOREWORD

- 1) The International Electrotechnical Commission (IEC) is a worldwide organization for standardization comprising all national electrotechnical committees (IEC National Committees). The object of IEC is to promote international co-operation on all questions concerning standardization in the electrical and electronic fields. To this end and in addition to other activities, IEC publishes International Standards, Technical Specifications, Technical Reports, Publicly Available Specifications (PAS) and Guides (hereafter referred to as "IEC Publication(s)"). Their preparation is entrusted to technical committees; any IEC National Committee interested in the subject dealt with may participate in this preparatory work. International, governmental and non-governmental organizations liaising with the IEC also participate in this preparation. IEC collaborates closely with the International Organization for Standardization (ISO) in accordance with conditions determined by agreement between the two organizations.
- 2) The formal decisions or agreements of IEC on technical matters express, as nearly as possible, an international consensus of opinion on the relevant subjects since each technical committee has representation from all interested IEC National Committees.
- 3) IEC Publications have the form of recommendations for international use and are accepted by IEC National Committees in that sense. While all reasonable efforts are made to ensure that the technical content of IEC Publications is accurate, IEC cannot be held responsible for the way in which they are used or for any misinterpretation by any end user.
- 4) In order to promote international uniformity, IEC National Committees undertake to apply IEC Publications transparently to the maximum extent possible in their national and regional publications. Any divergence between any IEC Publication and the corresponding national or regional publication shall be clearly indicated in the latter.
- 5) IEC itself does not provide any attestation of conformity. Independent certification bodies provide conformity assessment services and, in some areas, access to IEC marks of conformity. IEC is not responsible for any services carried out by independent certification bodies.
- 6) All users should ensure that they have the latest edition of this publication.
- 7) No liability shall attach to IEC or its directors, employees, servants or agents including individual experts and members of its technical committees and IEC National Committees for any personal injury, property damage or other damage of any nature whatsoever, whether direct or indirect, or for costs (including legal fees) and expenses arising out of the publication, use of, or reliance upon, this IEC Publication or any other IEC Publications.
- 8) Attention is drawn to the Normative references cited in this publication. Use of the referenced publications is indispensable for the correct application of this publication.
- 9) Attention is drawn to the possibility that some of the elements of this IEC Publication may be the subject of patent rights. IEC shall not be held responsible for identifying any or all such patent rights.

International Standard IEC 62047-36 has been prepared by subcommittee 47F: Micro-electromechanical systems, of IEC technical committee 47: Semiconductor devices.

The text of this International Standard is based on the following documents:

FDIS	Report on voting
47F/329/FDIS	47F/334/RVD

Full information on the voting for the approval of this International Standard can be found in the report on voting indicated in the above table.

This document has been drafted in accordance with the ISO/IEC Directives, Part 2.

A list of all parts in the IEC 62047 series, published under the general title *Semiconductor devices – Micro-electromechanical devices*, can be found on the IEC website.

The committee has decided that the contents of this document will remain unchanged until the stability date indicated on the IEC website under "<http://webstore.iec.ch>" in the data related to the specific document. At this date, the document will be

- reconfirmed,
- withdrawn,
- replaced by a revised edition, or
- amended.

A bilingual version of this publication may be issued at a later date.

IMPORTANT – The 'colour inside' logo on the cover page of this publication indicates that it contains colours, which are considered to be useful for the correct understanding of its contents. Users should therefore print this document using a colour printer.

INTRODUCTION

Piezoelectric MEMS technology belongs to an interdisciplinary field founded on a wide range of element technologies including piezoelectric thin film materials, thin film deposition and microfabrication processes, device design, and system formulation. Along with the increased sophistication of MEMS functionality, research on MEMS applications for piezoelectric thin films, such as $\text{Pb}(\text{Zr,Ti})\text{O}_3$ (PZT) or AlN , has become increasingly popular in recent years. MEMS piezoelectric thin films have the capability of configuring simple compact devices that have a lower power consumption, higher sensitivity, and quicker response than conventional bulk-type, electrostatic, or electromagnetic thin films. However, their device performance is greatly affected by the properties of the thin film materials.

Several test methods for thin film materials have been established to date. Among these, the overriding property that determines device performance is the material's piezoelectric property. Standardization of IEC 62047-30 (*Semiconductor devices – Micro-electromechanical devices – Part 30: Measurement methods of electro-mechanical conversion characteristics of MEMS piezoelectric thin film*) has been promoted for the purpose of precisely measuring and evaluating MEMS piezoelectric thin films using simply structured test pieces and inexpensive equipment.

In order to realize a viable MEMS piezoelectric thin film, it is essential to gain a clear understanding of how its piezoelectric properties change as a result of the environmental stress of temperature and humidity, and degradation in the piezoelectric material over time at its surfaces and interfaces. Achieving a viable MEMS piezoelectric thin film will also require a clear understanding of dielectric withstand for the electrical stress of a voltage (electric field) higher than the drive voltage (electric field) used for normal operations.

The following summarizes the features of this standard.

- The degree of degradation in a device under test (DUT) is evaluated by measuring the piezoelectric properties of the DUT before and after applying the environmental stress of temperature and humidity using the measurement methods in IEC 62047-30.
- Test conditions for moist heat and dielectric withstand tests are derived from existing standards for semiconductor devices and fixed capacitors of ceramic dielectric.
- The dielectric withstand property is evaluated by measuring the leakage current under the DC bias voltage.

SEMICONDUCTOR DEVICES – MICRO-ELECTROMECHANICAL DEVICES –

Part 36: Environmental and dielectric withstand test methods for MEMS piezoelectric thin films

1 Scope

This part of IEC 62047 specifies test methods for evaluating the durability of MEMS piezoelectric thin film materials under the environmental stress of temperature and humidity and under electrical stress, and test conditions for appropriate quality assessment. Specifically, this document specifies test methods and test conditions for measuring the durability of a DUT under temperature and humidity conditions and applied voltages. It further applies to evaluations of converse piezoelectric properties in piezoelectric thin films formed primarily on silicon substrates, i.e., piezoelectric thin films used as actuators.

This document does not cover reliability assessments, such as methods of predicting the lifetime of a piezoelectric thin film based on a Weibull distribution.

2 Normative references

The following documents are referred to in the text in such a way that some or all of their content constitutes requirements of this document. For dated references, only the edition cited applies. For undated references, the latest edition of the referenced document (including any amendments) applies.

IEC 62047-30, *Semiconductor devices – Micro-electromechanical devices – Part 30: Measurement methods of electro-mechanical conversion characteristics of MEMS piezoelectric thin film*

IEC 60068-2-14:2009, *Environmental testing – Part 2-14: Tests – Test N: Change of temperature*

3 Terms and definitions

No terms and definitions are listed in this document.

ISO and IEC maintain terminological databases for use in standardization at the following addresses:

- IEC Electropedia: available at <http://www.electropedia.org/>
- ISO Online browsing platform: available at <http://www.iso.org/obp>

4 Testing procedure

4.1 General

The degree of degradation in a device under test (DUT) is evaluated by measuring the piezoelectric properties of the DUT before and after applying the environmental stress of temperature and humidity. Figure 1 shows the general flow of the testing procedure.